

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

1-17 (Canceled)

18. (Currently Amended) A semiconductor laser manufacturing method comprising:  
forming a nitride semiconductor layer by a crystal growth ~~for crystallographically~~  
~~growing a nitride semiconductor~~ on a substrate;  
selectively etching said nitride semiconductor to form a stripe-shaped opening;  
forming a buried layer by crystallographically growing a nitride semiconductor  
containing at least two kinds of group III elements in and above said opening and on said  
nitride semiconductor layer; and  
~~for forming an active layer of a nitride semiconductor on said buried layer.~~

19. (Currently Amended) The semiconductor laser manufacturing method according to  
claim 18, wherein said buried layer is made of AlGaIn.

20. (Currently Amended) The semiconductor laser manufacturing method according to  
claim 18, wherein said nitride semiconductor layer is a layer which blocks part of a current  
injected into said active layer.

21. (Original) A semiconductor laser manufacturing method comprising:  
sequentially forming on a substrate an etching stop layer of a first conduction type  
nitride semiconductor, an etching layer of a nitride semiconductor and an etching mask layer of

a second conduction type nitride semiconductor, said nitride semiconductor of said etching layer being more likely etched than those of said etching mask layer and said etching stop layer;

partly etching said etching mask layer to form a stripe-shaped first opening to expose a part of said etching layer in said first opening;

heating said etching layer in a mixed atmosphere containing hydrogen and at least one of nitrogen, ammonium, helium, argon, xenon and neon, or a mixed atmosphere of nitrogen and ammonium, or a hydrogen atmosphere to etch said etching layer exposed in said first opening and thereby form a stripe-shaped second opening to expose a part of said etching stop layer;

burying said first opening and said second opening with a buried layer of a first conduction type nitride semiconductor; and

forming an active layer on said buried layer.

22. (Currently Amended) The semiconductor laser manufacturing method according to claim 21, wherein said etching stop layer is made of  $\text{Al}_y\text{Ga}_{1-y}\text{N}$  ( $0.05 \leq x \leq 0.3$ ), said etching mask layer is made of  $\text{Al}_y\text{Ga}_{1-y}\text{N}$  ( $0.05 \leq y \leq 1$ ,  $x \leq y$ ), and said etching layer is made of  $\text{Al}_y\text{Ga}_{1-y}\text{N}$  ( $0 \leq z < 0.3$ ,  $z < x$ ).

23. (Currently Amended) The semiconductor laser manufacturing method according to claim 22, wherein the temperature of heating said etching layer is higher than  $800^\circ\text{C}$  and does not exceeds  $1150^\circ\text{C}$ .

24. (Currently Amended) The semiconductor laser manufacturing method according to claim 21, wherein said etching stop layer is made of  $\text{In}_x\text{Ga}_{1-x}\text{N}$  ( $0 \leq x \leq 0.05$ ), said etching mask layer is made of  $\text{In}_y\text{Ga}_{1-y}\text{N}$  ( $0 \leq y \leq 0.05$ ), and said etching layer is made of  $\text{In}_z\text{Ga}_{1-z}\text{N}$  ( $0.05 \leq z \leq 0.3$ ,  $z > x$ ,  $z > y$ ).

25. (Currently Amended) The semiconductor laser manufacturing method according to claim 24, wherein the temperature of heating said etching layer is in the range from  $600^\circ\text{C}$  to  $800^\circ\text{C}$ .

26.-28. (Canceled)